

SCHOTTKY DIODES

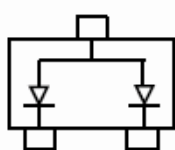
FEATURES

Fast Switching Speed

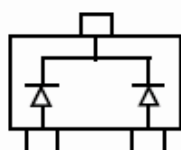
For General Purpose Switching Applications

High Conductance

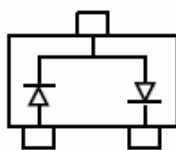
MARKING:



BAW56:A1



BAV70:A4



BAV99:A7

BAW56/BAV70/BAV99



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Reverse voltage	V	70	V
Forward Current	I	200	mA
Peak Forward Surge Current	IFM(surge)	500	mA
Power Dissipation	P	225	mW
Thermal Resistance Junction to Ambient Air	RθJ	556	°C/W
Junction temperature	T	150	°C
Storage temperature range	TST	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _R	70			V	I _R =100μA
Forward voltage	V _{F1}			0.715	V	I _F =1mA
	V _{F2}			0.855	V	I _F =10mA
	V _{F3}			1	V	I _F =50mA
	V _{F4}			1.25	V	I _F =150mA
Reverse current	I _R			2.5	μA	V _R =70V
Capacitance between terminals	C _T			1.5	pF	V _R =0, f=1MHz
Reverse recovery time	t _{rr}			6	ns	I _F = I _R = 10mA, I _{rr} = 0.1 x I _R , R _L = 100Ω

BAW56/BAV70/BAV99 Typical Characteristics

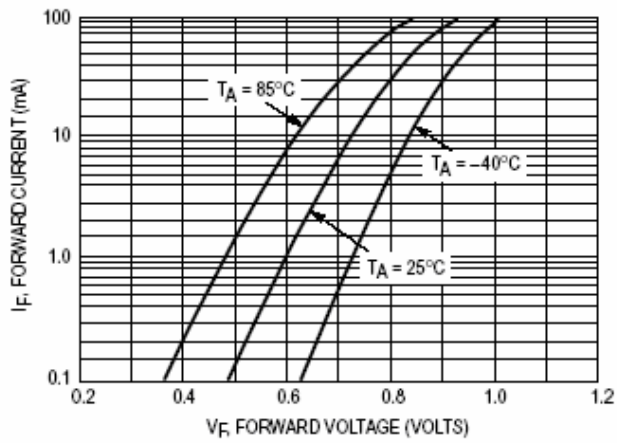


Figure 1. Forward Voltage

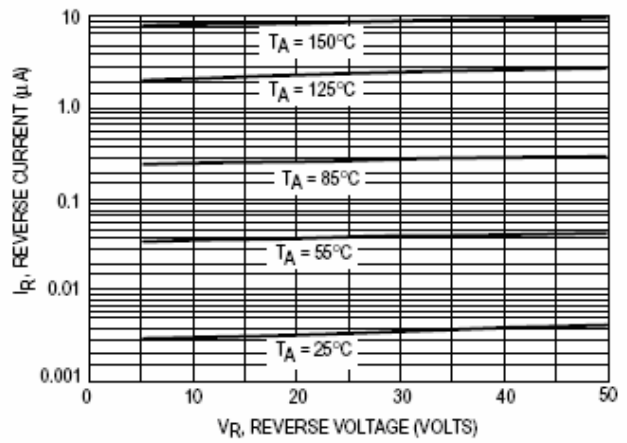


Figure 2 Leakage Current

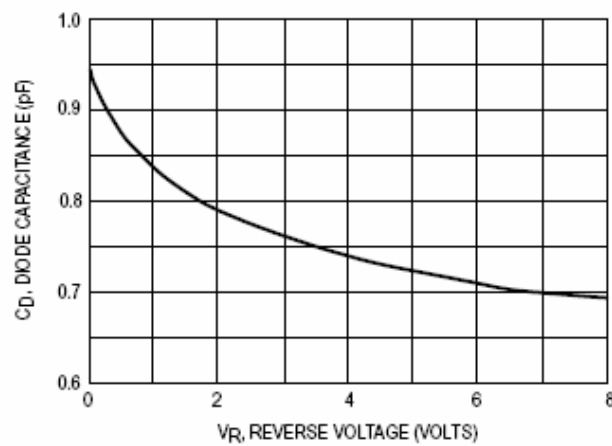


Figure 3 Capacitance